SIC MOSFET

Description

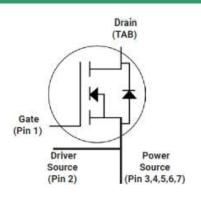
MOSFET Product Summary					
V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)			
1700	750@ V _{GS} = 12V	5			

Feature

- ➤ High Speed Switching with Low Capacitances
- Lower QG and Device Capacitances(Coss,Crss)
- > Body Diode with Low VF and Low QRR
- > Faster and More Efficient Switching
- > ROHS Compliant, Halogen free

Applications

- Solar String Inveter and Central Inverter
- > UPS
- Switch Mode Power Supplies
- Power Factor Correction Modules
- Battery Charging
- Auxiliary Power Supply
- > High Voltage Coverter



Schematic diagram



TO-263-7

Absolute maximum rating@25°C

Parameter	Symbol	Rating	Unit		
Drain-Source Voltage	V _{DS}	1700	٧		
Gate-Source Voltage	V _{GS}	-5/+15	V		
Continuous Dusin Current @ V45V	T _C =25°C		5	Α	
Continuous Drain Current @ V _{GS} =15V	T _C =100°C	l _D	3		
Pulsed Drain Current	I _{DM}	10	А		
Power Dissipation	P _D	60	W		
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to +175	°C		

Thermal Resistance

Parameter	Symbol	Min	Тур	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	-	-	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	-	-	40	°C/W

PSICM7D2P170R750

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	I Conditions		Тур.	Max.	Units	
Statistic Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_{D} = 100 \mu A$	1700	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 1700V,V _{GS} = 0V	-	-	100	μΑ	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =-5V to 15V,V _{DS} =0V	-	-	100	nA	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 1mA$	1.5	2	3	V	
Recommended turn-on Voltage	V_{GSon}	C4-4:-	-	12	-	V	
Recommended turn-off Voltage	V_{GSoff}	Static	-	-3	-		
	_	V _{GS} = 12V,I _D = 2A	-	750	1000	_	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 12V,I _D = 2A T _{.J} =175°C	-	1350	-	mΩ	
Dynamic Characteristics		J					
Input Capacitance	C _{lss}		-	200	-	pF	
Output Capacitance	C _{oss}	V_{DS} =1000V, V_{AC} =25 mV, f = 1MHz	-	6	-		
Reverse Transfer Capacitance	C _{rss}	1 1111112	-	1	-		
Transconductance	g _{fs}	$V_{DS} = 10V, I_{D} = 2A$	-	1	-	S	
C _{OSS} Stored Energy	E _{oss}	V _{DS} =1000V, f = 1MHz	-	3	-	μJ	
Turn-On Switching Energy	E _{on}	$V_{DS} = 1200V, I_{D} = 2A$	-	27	-	μJ	
Turn-Off Switching Energy	E _{off}	V _{GS} = -3/+12V, L=1mH, T _J =175°C	-	8.4	-		
Turn-on Delay Time	t _{d(on)}		-	11	-	ns	
Turn-on Rise Time	t _r	$V_{DS} = 1200V, I_{D} = 2A$	-	7	-		
Turn-Off Delay Time	t _{d(off)}	$V_{GS} = -3/+12V$, $R_{ext} = 25\Omega$,L=1mH	-	9	-		
Turn-Off Fall Time	t _f		-	6	-		
Total Gate Charge	Q_g		-	8	-		
Gate-Source Charge	Q_{gs}	$V_{DS} = 1200V, I_{D} = 2A,$ $V_{GS} = -3/+12V$	-	1.5	-	nC	
Gate-Drain Charge	Q_{gd}	VGS OF 12V	-	3	-		
Reverse Diode Characteristics							
Famurand Voltage		V _{GS} =0V,I _F = 1A,T _J =25°C	-	3.5	6.0	V	
Forward Voltage	V _{FSD}	V _{GS} =0V,I _F = 1A,T _J =175°C	-	3.0	6.0	V	
Continuous Diode Forward Current	I _s	V _{GS} =0V	-	5	-	Α	

Typical Characteristics

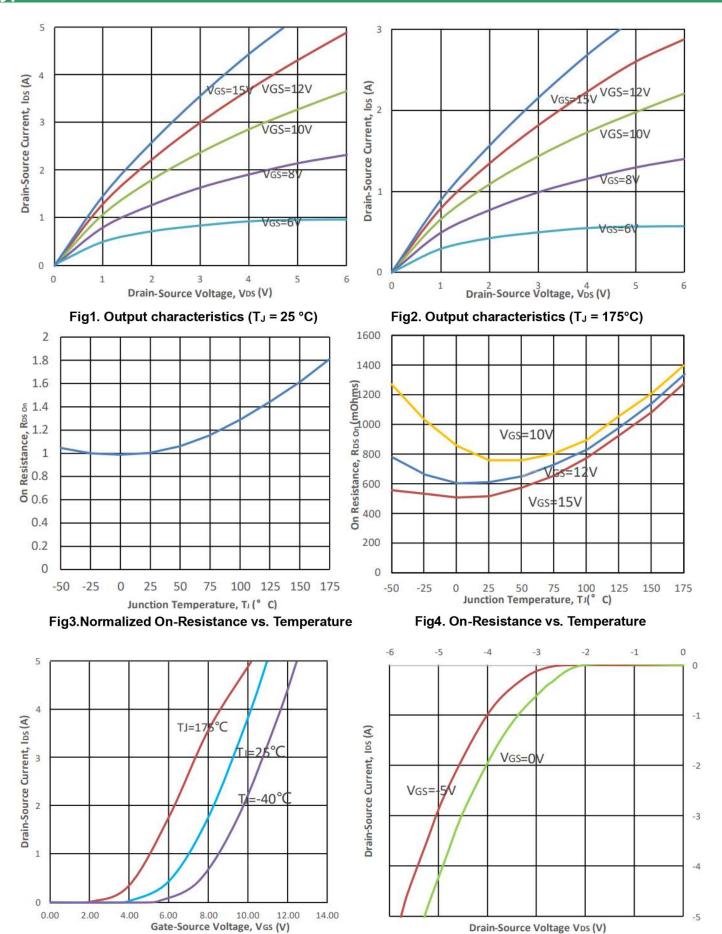


Fig5. Transfer Characteristic

Fig6. Body Diode Characteristic at 25 °C

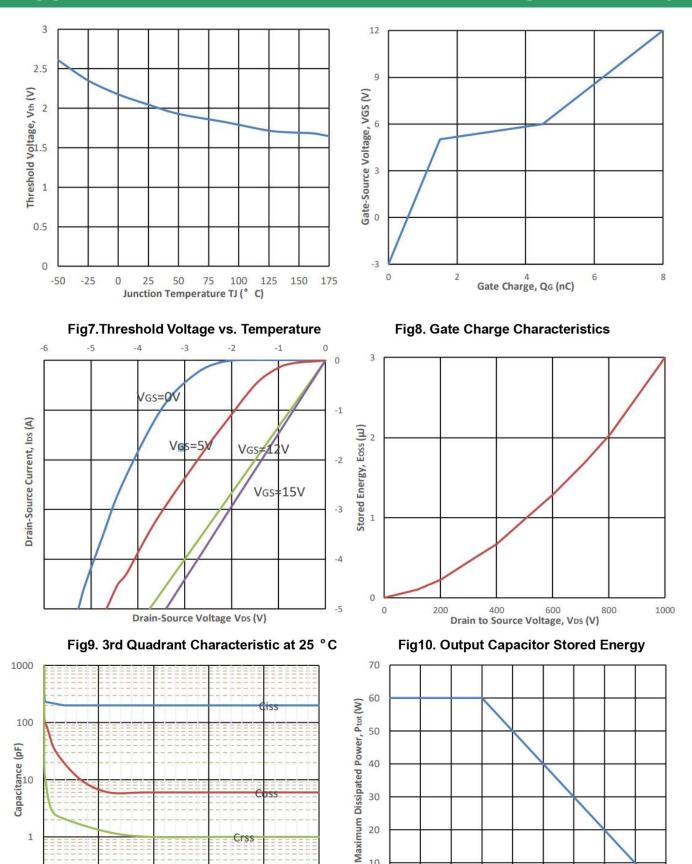


Fig11. Capacitances vs. Drain-Source

400 600 Drain-Source Voltage, VDS (V)

1

0.1

0

Fig12. Max Power Dissipation Derating Vs Tc

25 50 75 100 Case Temperature, Tc (° C)

150

1000

20

10

0

-50

-25

0

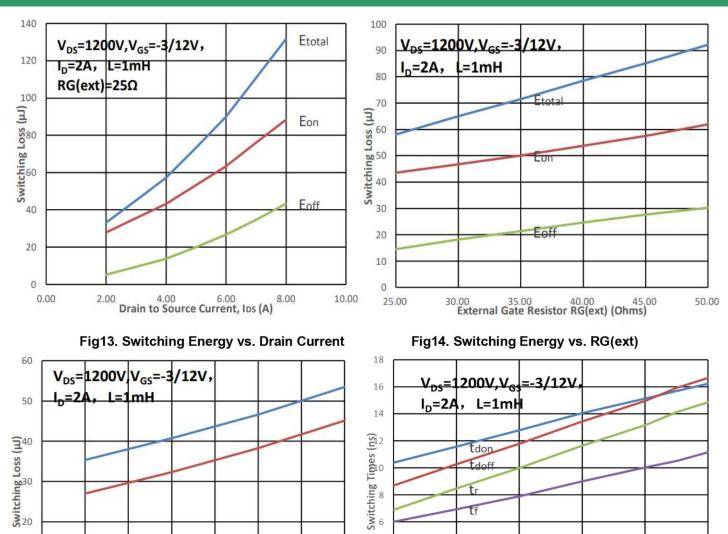


Fig15. Swit ching Energy vs. Temperature

50.00 75.00 100.00 125.00 Junction Temperature, TJ (°C)

Fig16. Switching Times vs. RG(ext) 10 Junction To Case Impedance, ZthJC (oC/W) Ous Drain-Source Current, Ibs (A) 0.1 100us 0.02 0.01 ms SinglePulse 100 ms 0.01 1.E-06 1.E-05 1.E-04 1.E-03 1.E-02 1.E-01 1.E+00 0.1 10 1000 Drain-Source Voltage, VDS (V) Time, tp (s)

25.00

150.00

30.00

35.00

40.00

External Gate Resistor RG(ext) (Ohms)

45.00

50.00

Fig17.Transient Thermal Impedance

10

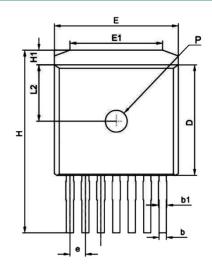
0

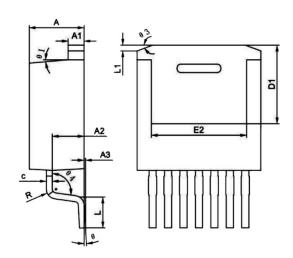
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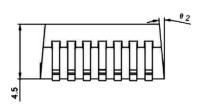
25.00

SIC MOSFET

Product dimension (TO-267-7L)







Dive	Millimeters			Dim	Millimeters			
Dim	Min	Туре	Max	Dim	Min	Type	Max	
А	4.40	4.50	4.60	е	1.17	1.27	1.37	
A1	1.25	1.30	1.40	Н	14.75	15.00	15.25	
A2	2.45	2.60	2.70	H1	1.10	1.20	1.30	
A3	0.05	0.13	0.20	L	2.35	2.55	2.75	
b	0.50	0.60	0.70	L1	0.37	0.57	0.77	
b1	0.60	0.70	0.85	L2	4.48	4.63	4.78	
С	0.45	0.50	0.60	θ	0°	3°	5°	
D	8.88	9.08	9.28	θ1	3°	5°	7°	
D1	6.25	6.45	6.65	θ2	3°	5°	7°	
E	9.88	10.18	10.28	θ3	15°	20°	25°	
E1	6.67	7.07	7.47	R	0.75	0.80	0.85	
E2	7.67	7.82	7.97	Р	1.70	1.80	1.90	

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